

Silicon NPN Power Transistors

2SC508

DESCRIPTION

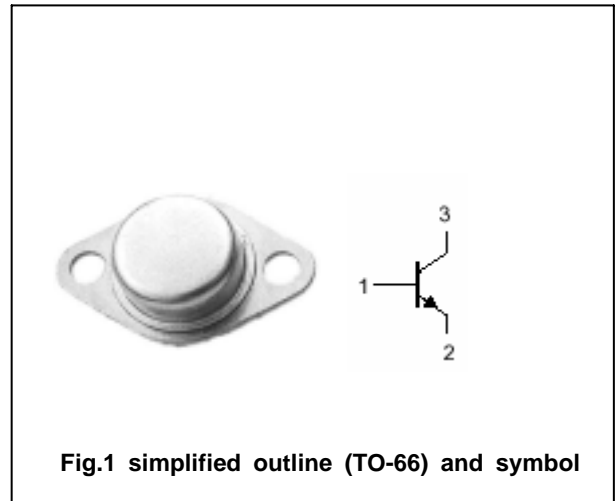
- With TO-66 package
- High collector-base breakdown voltage
: $V_{CBO}=180V(\text{min})$

APPLICATIONS

- For power switching and TV horizontal output applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	180	V
V_{CEO}	Collector-emitter voltage	Open base	60	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		4	A
P_D	Total power dissipation	$T_C=25$	25	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~200	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =30mA; I _B =0	60			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA; I _E =0	180			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.4 A			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.4 A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =180V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			100	μA
h _{FE}	DC current gain	I _C =4A; V _{CE} =5V	20			

PACKAGE OUTLINE

